

# MMCFD914

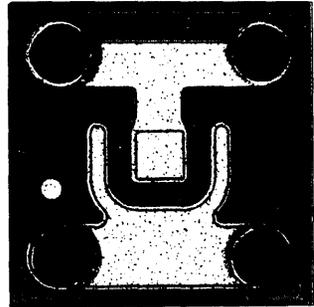
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Flip-Chip diode for high-speed switching applications with performance similar to the 1N914.

Primary Electrical Features:

- Breakdown Voltage –  $V_{(BR)} = 100V$  (Min)
- Forward Current – to 225 mAdc
- Reverse Recovery time –  $t_{rr} \leq 5.0$  ns

## FLIP-CHIP SWITCHING DIODE



### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	$V_R$	100	Vdc
Forward Current	$I_F$	225	mAdc
Forward Surge Current	$I_F(\text{surge})$	500	mAdc

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Breakdown Voltage ( $I_{(BR)} = 10 \mu\text{Adc}$ )	$V_{(BR)}$	100	—	Vdc
Reverse Current ( $V_R = 20$ Vdc)	$I_R$	—	50	nAdc
Forward Voltage ( $I_F = 10$ mAdc)	$V_F$	—	1.0	Vdc
Capacitance ( $V_R = 0$ )	C	—	5.0	pF
Reverse Recovery Time ( $I_F = 10$ mAdc, $V_R = 6.0$ Vdc, $i_{rr} = 1.0$ mAdc)	$t_{rr}$	—	5.0	ns